

AMENDMENT TO CLAIMS

1. (Currently amended) A method for fabricating a nitride semiconductor laser device, which comprises;

a first step to form a multi-layered semiconductor on a substrate, the multi-layered semiconductor containing at least an n-type nitride semiconductor layer, an active layer, and a p-type nitride semiconductor layer;

a second step to expose the surfaces of the n-type nitride semiconductor layer and the p-type nitride semiconductor layer at different heights by selectively etching the multi-layered semiconductor;

a third step to cover the surface of the multi-layered semiconductor, including the exposed surfaces of the n-type nitride semiconductor layer and the p-type nitride semiconductor layer, with an insulating film that has a thickness greater than the difference in levels between the exposed surface of the n-type nitride semiconductor layer and the outermost surface of the p-type nitride semiconductor layer;

a fourth step to flatten the surface of the insulating film; and

a fifth step to form an n-type electrode and a p-type electrode that are electrically connected to the n-type nitride semiconductor layer and the p-type nitride semiconductor layer, respectively, through the insulating film, wherein

the exposed surfaces of the n-type electrode and the p-type electrode are formed on the same flattened surface of the insulating film.

2. (Original) The method for fabricating a nitride semiconductor laser device according to Claim 1, which further comprises;

a sixth step, following the fifth step, to press-fit the surface of the insulating film to a sub-mount containing a first wire and a second wire by using heat-melted solder structures and electrically connect the n-type electrode and the p-type electrode to the first wire and the second wire, respectively.

3. (Original) The method for fabricating a nitride semiconductor laser device according to Claim 1, wherein the insulating film contains fine-grains of a metal or a semiconductor.

4-5. (Cancelled)

6. (Previously presented) The method for fabricating a nitride semiconductor laser device according to Claim 1, wherein, in the fifth step, the n-type electrode and the p-type electrode are formed so as to be connected to the exposed surfaces of the n-type nitride semiconductor layer and the p-type nitride semiconductor layer, respectively.

7. (Cancelled)